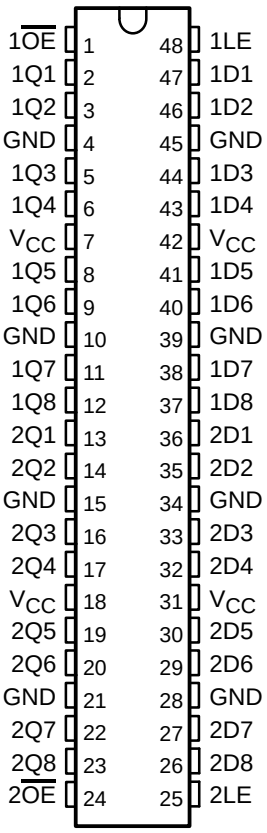
- **Members of the Texas Instruments *Widebus*™ Family**
- **High-Impedance State During Power Up and Power Down**
- **5-V I/O Compatible**
- **High-Drive Capability (–32 mA/64 mA)**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Auto 3-State Eliminates Bus Current Loading When Voltage at the Output Exceeds V_{CC}**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup/Pulldown Resistors**
- **Power Off Disables Inputs/Outputs, Permitting Live Insertion**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package**

SN54ALVTH16373 . . . WD PACKAGE
SN74ALVTH16373 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

The ’ALVTH16373 are 16-bit transparent D-type latches with 3-state outputs designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

PRODUCT PREVIEW

description (continued)

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

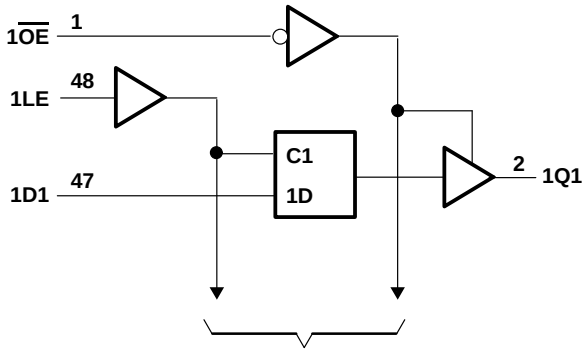
The SN74ALVTH16373 is available in TI's thin very small-outline package (DGV), which provides the same I/O pin count and functionality of standard Widebus packages in less than half the printed circuit board area.

The SN54ALVTH16373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH16373 is characterized for operation from –40°C to 85°C.

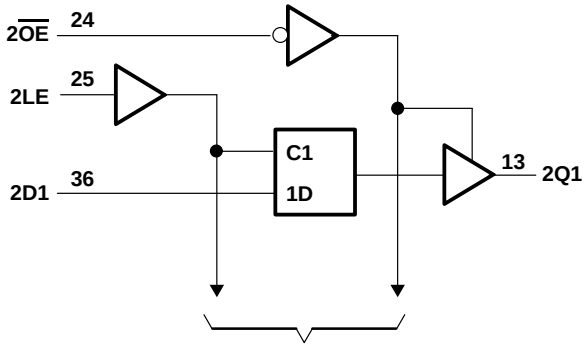
FUNCTION TABLE
(each 8-bit section)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic diagram (positive logic)



To Seven Other Channels



To Seven Other Channels

PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) . . . . –0.5 V to 7 V
Output current in the low state, I_O: SN54ALVTH16373 . . . . . 96 mA
SN74ALVTH16373 . . . . . 128 mA
Output current in the high state, I_O: SN54ALVTH16373 . . . . . –48 mA
SN74ALVTH16373 . . . . . –64 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DGG package . . . . . 0.85 W
DGV package . . . . . 0.87 W
DL package . . . . . 1.2 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*.

recommended operating conditions, V_{CC} = 2.5 V ± 0.2 V (see Note 3)

			SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.3	2.7	2.3	2.7	V
V_{IH}	High-level input voltage		1.7		1.7		V
V_{IL}	Low-level input voltage			0.7		0.7	V
V_I	Input voltage		0	5.5	0	5.5	V
I_{OH}	High-level output current			–6		–8	mA
I_{OL}	Low-level output current			6		8	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 KHz			18		24	
Δt/Δv	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused control inputs must be held high or low to prevent them from floating.

recommended operating conditions, V_{CC} = 3.3 V ± 0.3 V (see Note 3)

			SN54ALVTH16373		SN74ALVTH16373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		3	3.6	3	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	5.5	0	5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			24		32	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 KHz			48		64	
Δt/Δv	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	TEST CONDITIONS			SN54ALVTH16373			SN74ALVTH16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.3 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = 2.3 V to 2.7 V,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.3 V	I_{OH} = – 6 mA		1.7						
		I_{OH} = – 8 mA					1.7			
V_{OL}	V_{CC} = 2.3 V to 2.7 V,	I_{OL} = 100 µA				0.2			0.2	V
	V_{CC} = 2.3 V	I_{OL} = 6 mA				0.5				
		I_{OL} = 8 mA							0.5	
		I_{OL} = 18 mA				0.5				
		I_{OL} = 24 mA							0.5	
I_I	V_{CC} = 2.7 V,	V_I = GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or 2.7 V,	V_I = 2.7 V	Control inputs			10			10	
	V_{CC} = 2.7 V	V_I = V_{CC}	Data inputs			10			10	
		V_I = 0	Data inputs			–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V				±100			±100	µA
$I_{I(hold)}$	V_{CC} = 2.3 V	V_I = 0.7 V	Data inputs		90			90		µA
		V_I = 1.7 V	Data inputs		75			75		
	V_{CC} = 2.7 V‡,	V_I = 0 to 2.7 V	Data inputs							
I_{EX}§	V_{CC} = 2.3 V,	V_O = 3.6 V								µA
$I_{OZ(PU/PD)}$¶	V_{CC} ≤ 1.2 V, V_I = GND or V_{CC},	$\overline{V_O}$ = 0.5 V to V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}	V_{CC} = 2.7 V, V_O = 2.7 V, V_I = 0.7 V or 1.7 V					5			5	µA
I_{OZL}	V_{CC} = 2.7 V, V_O = 0 V, V_I = 0.7 V or 1.7 V					–5			–5	µA
I_{CC}	V_{CC} = 2.7 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.04	0.09		0.04	0.09	mA
			Outputs low		2.3	4.5		2.3	4.5	
			Outputs disabled		0.04	0.09		0.04	0.09	
C_i	V_{CC} = 2.5 V,	V_I = 2.5 V or 0			3			3		pF
C_o	V_{CC} = 2.5 V,	V_O = 2.5 V or 0			9			9		pF

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ Current into an output in the high state when $V_O > V_{CC}$
¶ High-impedance state during power up/high-impedance state during power down

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	TEST CONDITIONS			SN54ALVTH16373			SN74ALVTH16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 3 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = 3 V to 3.6 V,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = – 32 mA					2			
V_{OL}	V_{CC} = 3 V to 3.6 V,	I_{OL} = 100 µA				0.2			0.2	V
	V_{CC} = 3 V	I_{OL} = 16 mA							0.4	
		I_{OL} = 24 mA				0.5				
		I_{OL} = 32 mA							0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or 3.6 V,	V_I = 5.5 V	Control inputs			10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	Data inputs			20			20	
		V_I = V_{CC}	Data inputs			10			10	
		V_I = 0	Data inputs			–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V				±100			±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V	Data inputs	–75			–75			
	V_{CC} = 3.6 V‡,	V_I = 0 to 3.6 V	Data inputs			±500			±500	
I_{EX}§	V_{CC} = 3 V,	V_O = 5.5 V				125			125	µA
$I_{OZ(PU/PD)}$¶	V_{CC} ≤ 1.2 V, V_I = GND or V_{CC},	V_O = 0.5 V to V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{OZH}	V_{CC} = 3.6 V, V_O = 3 V, V_I = 0.8 V or 2 V					5			5	µA
I_{OZL}	V_{CC} = 3.6 V, V_O = 0.5 V, V_I = 0.8 V or 2 V					–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.07	0.09		0.07	0.09	mA
			Outputs low		3.2	5		3.2	5	
			Outputs disabled		0.07	0.09		0.07	0.09	
ΔI_{CC}#	V_{CC} = 3 V to 3.6 V, One input at V_{CC} –0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_{CC} = 3.3 V,	V_I = 3.3 V or 0			3			3		pF
C_o	V_{CC} = 3.3 V,	V_O = 3.3 V or 0			9			9		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ Current into an output in the high state when V_O > V_{CC}
¶ High-impedance state during power up/high-impedance state during power down
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW

timing requirements over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

		SN54ALVTH16373		SN74ALVTH16373		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	1.5		1.5		ns
t_{su}	Setup time, data before LE↓	1.1		1.1		ns
t_h	Hold time, data after LE↓	0.4		0.4		ns

timing requirements over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

		SN54ALVTH16373		SN74ALVTH16373		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	1.5		1.5		ns
t_{su}	Setup time, data before LE↓	0.8		0.8		ns
t_h	Hold time, data after LE↓	0.5		0.5		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16373		SN74ALVTH16373			UNIT
			MIN	MAX	MIN	TYP†	MAX	
t_{pd}	D	Q	1.2	4.7	1.2	2.4	4.2	ns
	LE	Q	1.8	6	1.8	2.8	5.4	
t_{en}	$\overline{OE}$	Q	2	6.5	2	3.4	5.9	ns
t_{dis}	$\overline{OE}$	Q	2	6.2	2	3.5	5.6	ns

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.

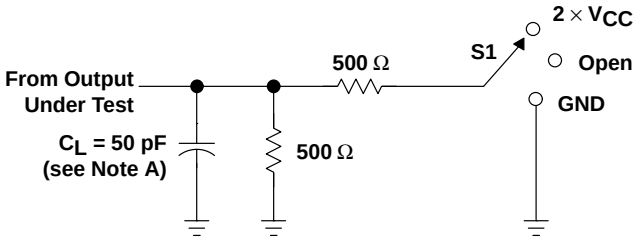
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16373		SN74ALVTH16373			UNIT
			MIN	MAX	MIN	TYP‡	MAX	
t_{pd}	D	Q	1	3.3	1	1.8	3	ns
	LE	Q	1.5	4	1.5	2.3	3.6	
t_{en}	$\overline{OE}$	Q	1.5	4.8	1.5	2.6	4.3	ns
t_{dis}	$\overline{OE}$	Q	1.5	4.7	1.5	2.7	4.2	ns

‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

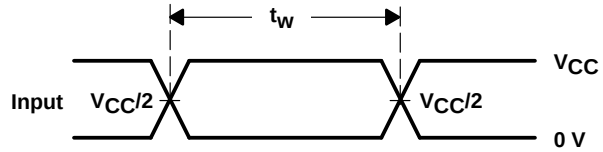
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

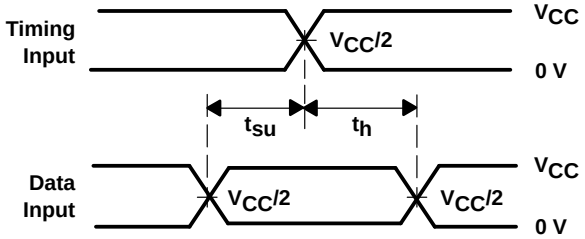


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

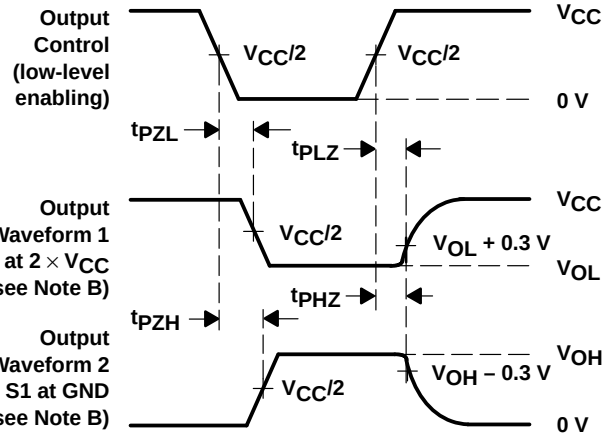
LOAD CIRCUIT



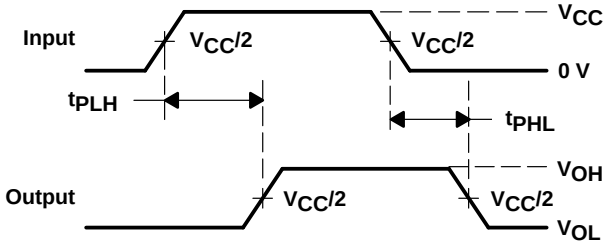
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES



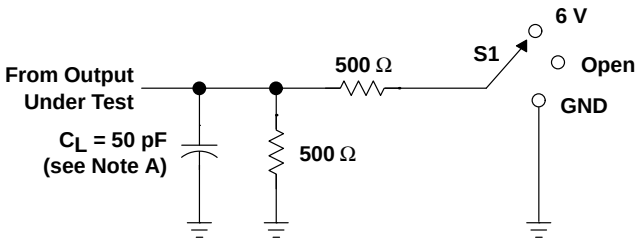
VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

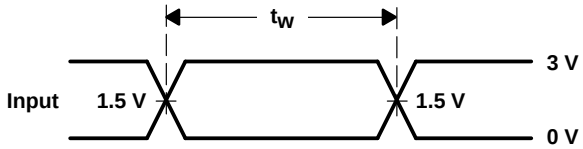
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

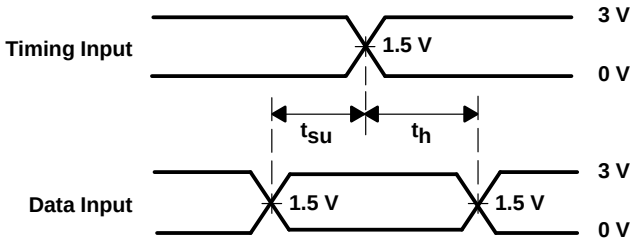


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

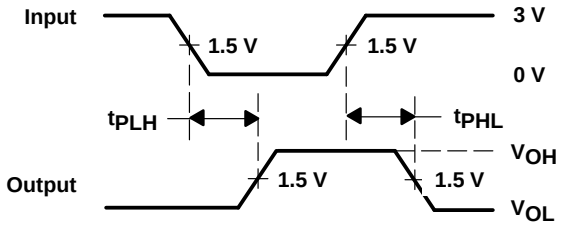
LOAD CIRCUIT



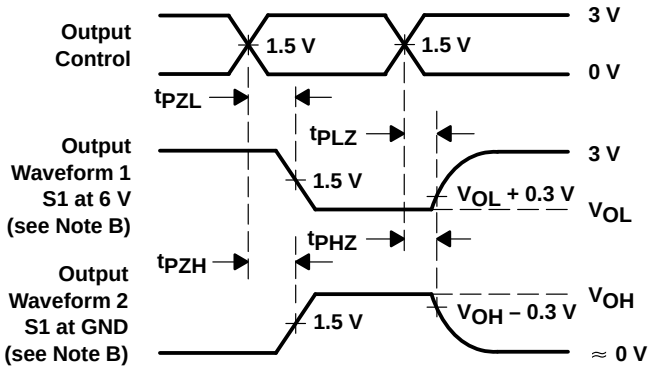
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

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